



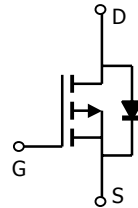
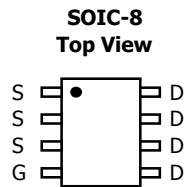
**AO4407, AO4407L (Lead-Free)  
P-Channel Enhancement Mode Field Effect Transistor**

**General Description**

The AO4407 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications. AO4407L is offered in a lead-free package.

**Features**

$V_{DS} (V) = -30V$   
 $I_D = -12 A$   
 $R_{DS(ON)} < 13m\Omega (V_{GS} = -20V)$   
 $R_{DS(ON)} < 14m\Omega (V_{GS} = -10V)$



**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 25$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ C$ $T_A=70^\circ C$	$I_D$	-12
			-10
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-60	A
Power Dissipation <sup>A</sup>	$T_A=25^\circ C$ $T_A=70^\circ C$	$P_D$	3
			2.1
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	28	40	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	54	75
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	21	30	$^\circ C/W$

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$ , $V_{GS}=0\text{V}$	-30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 25\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=-250\mu\text{A}$	-1.7	-2.5	-3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$ , $V_{DS}=-5\text{V}$	60			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$ , $I_D=-10\text{A}$ $T_J=125^\circ\text{C}$		11 15	14 19	$\text{m}\Omega$
		$V_{GS}=-20\text{V}$ , $I_D=-10\text{A}$		10	13	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$ , $I_D=-10\text{A}$		24		$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=-5\text{V}$ , $I_D=-10\text{A}$		26		S
$V_{SD}$	Diode Forward Voltage	$I_S=-1\text{A}$ , $V_{GS}=0\text{V}$		-0.72	-1	V
$I_S$	Maximum Body-Diode Continuous Current				-4.2	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=-15\text{V}$ , $f=1\text{MHz}$		2076	2500	pF
$C_{oss}$	Output Capacitance			503		pF
$C_{riss}$	Reverse Transfer Capacitance			302		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		2	3	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=-10\text{V}$ , $V_{DS}=-15\text{V}$ , $I_D=-12\text{A}$		37.2	45	nC
$Q_{gs}$	Gate Source Charge			7		nC
$Q_{gd}$	Gate Drain Charge			10.4		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=-10\text{V}$ , $V_{DS}=-15\text{V}$ , $R_L=1.25\Omega$ , $R_{GEN}=3\Omega$		12.4		ns
$t_r$	Turn-On Rise Time			8.2		ns
$t_{D(off)}$	Turn-Off Delay Time			25.6		ns
$t_f$	Turn-Off Fall Time			12		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=-12\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		33	40	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=-12\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		23		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any a given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

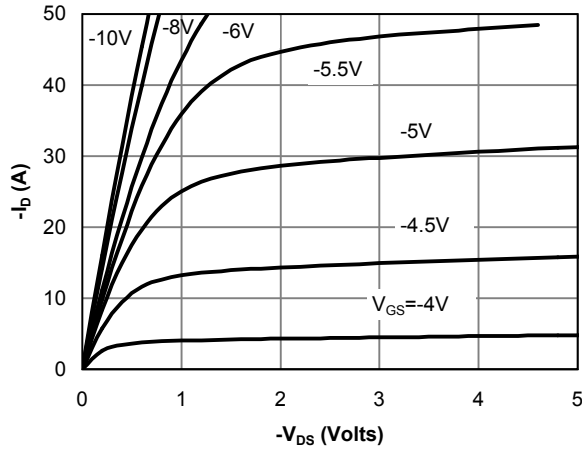


Fig 1: On-Region Characteristics

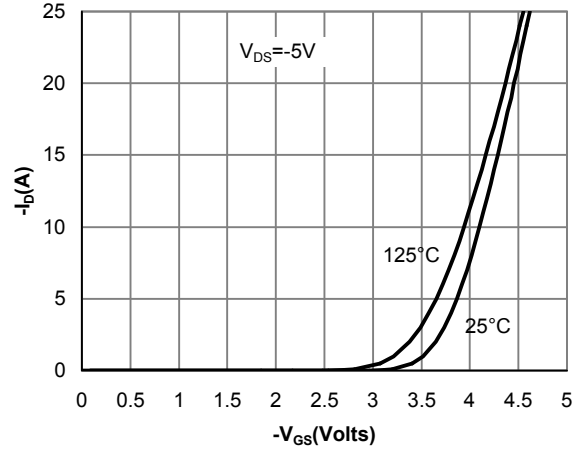


Figure 2: Transfer Characteristics

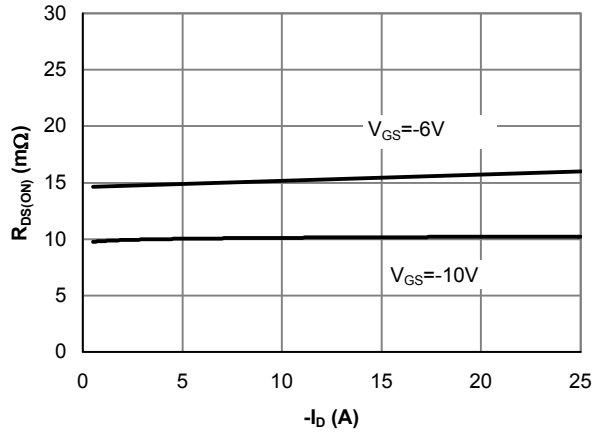


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

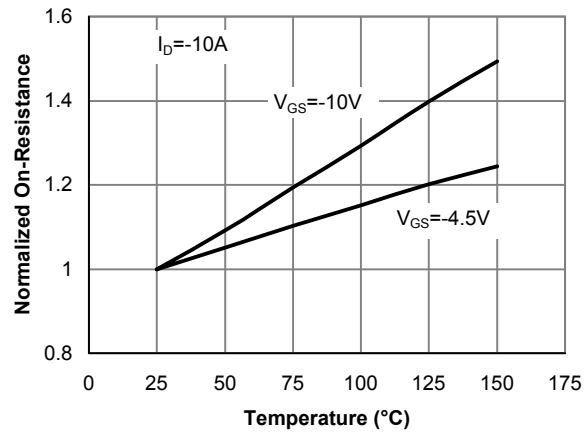


Figure 4: On-Resistance vs. Junction Temperature

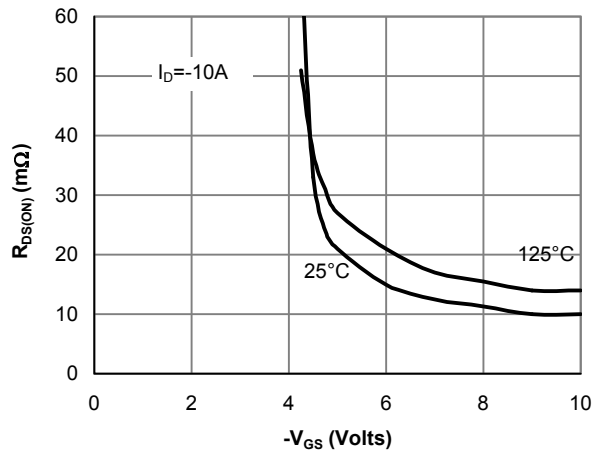


Figure 5: On-Resistance vs. Gate-Source Voltage

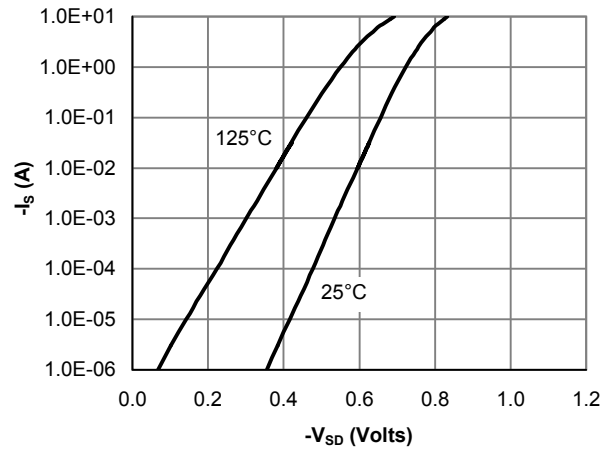


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

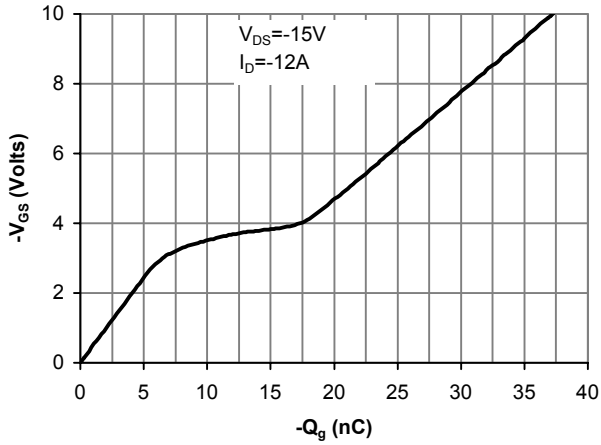


Figure 7: Gate-Charge Characteristics

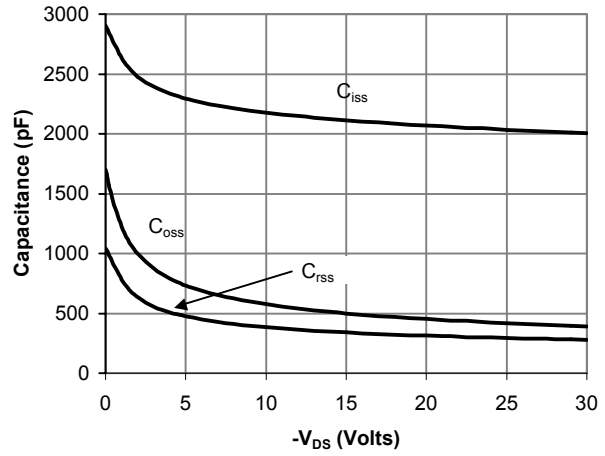


Figure 8: Capacitance Characteristics

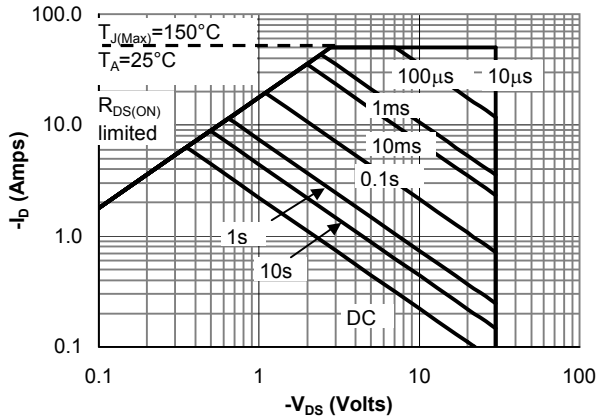


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

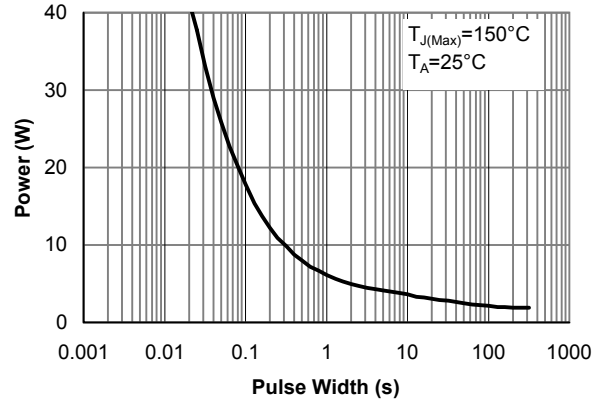


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

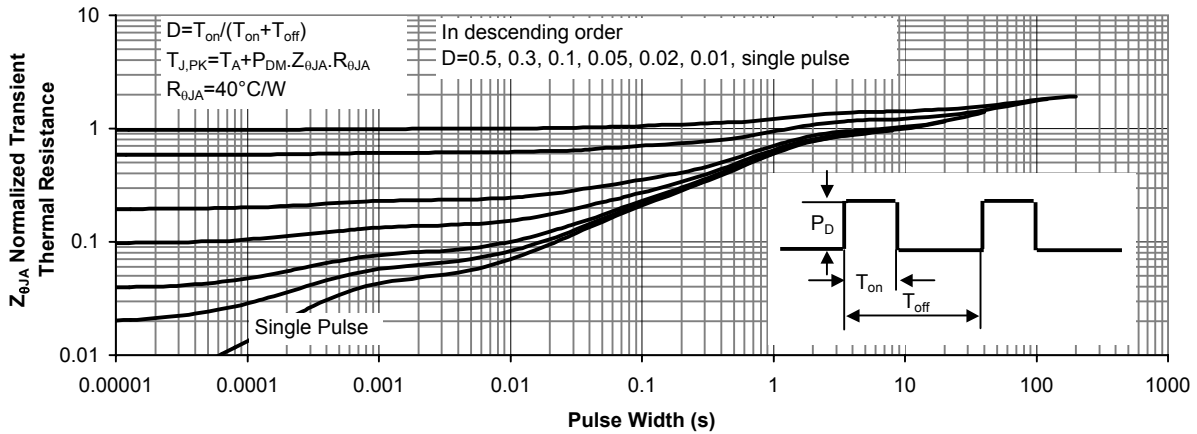
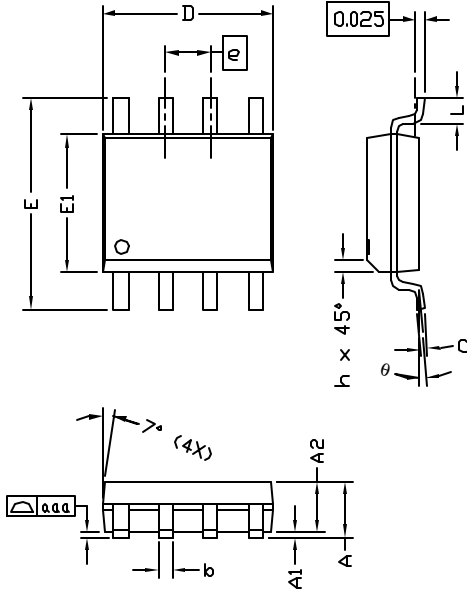


Figure 11: Normalized Maximum Transient Thermal Impedance



**ALPHA & OMEGA**  
SEMICONDUCTOR, INC.

## SOP-8 Package Data

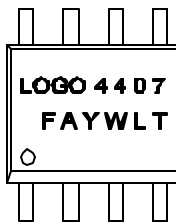


SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.45	1.50	1.55	0.057	0.059	0.061
A1	0.00	—	0.10	0.000	—	0.004
A2	—	1.45	—	—	0.057	—
b	0.33	—	0.51	0.013	—	0.020
c	0.19	—	0.25	0.007	—	0.010
D	4.80	—	5.00	0.189	—	0.197
E1	3.80	—	4.00	0.150	—	0.157
e	1.27 BSC			0.050 BSC		
E	5.80	—	6.20	0.228	—	0.244
h	0.25	—	0.50	0.010	—	0.020
L	0.40	—	1.27	0.016	—	0.050
aaa	—	—	0.10	—	—	0.004
θ	0°	—	8°	0°	—	8°

**NOTE:**

1. LEAD FINISH: 150 MICROINCHES ( 3.8 um) MIN. THICKNESS OF Tin/Lead (SOLDER) PLATED ON LEAD
2. TOLERANCE ±0.10 mm (4 mil) UNLESS OTHERWISE SPECIFIED
3. COPLANARITY : 0.10 mm
4. DIMENSION L IS MEASURED IN GAGE PLANE

### PACKAGE MARKING DESCRIPTION

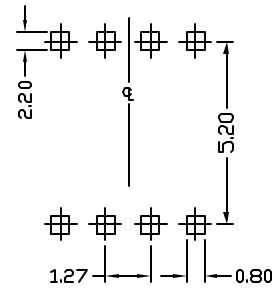


- NOTE:**
- LOGO - AOS LOGO
  - 4407 - PART NUMBER CODE.
  - F - FAB LOCATION
  - A - ASSEMBLY LOCATION
  - Y - YEAR CODE
  - W - WEEK CODE
  - L N - ASSEMBLY LOT CODE

### SOP-8 PART NO. CODE

PART NO.	CODE
AO4407	4407

### RECOMMENDED LAND PATTERN



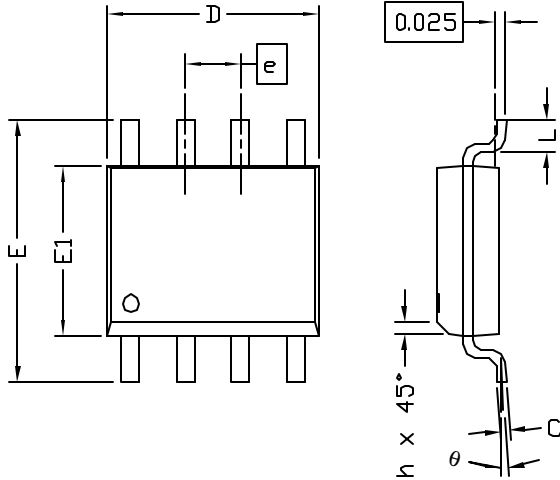
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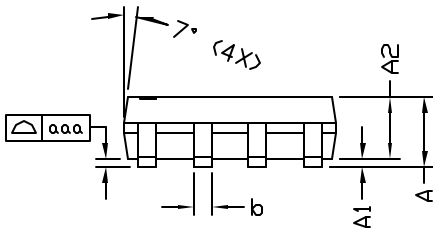
**ALPHA & OMEGA**  
SEMICONDUCTOR, INC.

Document No.	PD-00111
Version	rev B
Title	AO4407L Package Data Sheet

**SO-8 LEAD FREE**

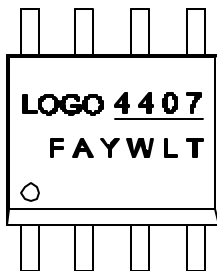


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A	1.45	1.50	1.55	0.057	0.059	0.061
A1	0.00	—	0.10	0.000	—	0.004
A2	—	1.45	—	—	0.057	—
b	0.33	—	0.51	0.013	—	0.020
c	0.19	—	0.25	0.007	—	0.010
D	4.80	—	5.00	0.189	—	0.197
E1	3.80	—	4.00	0.150	—	0.157
e	1.27 BSC			0.050 BSC		
E	5.80	—	6.20	0.228	—	0.244
h	0.25	—	0.50	0.010	—	0.020
L	0.40	—	1.27	0.016	—	0.050
aaa	—	—	0.10	—	—	0.004
θ	0°	—	8°	0°	—	8°



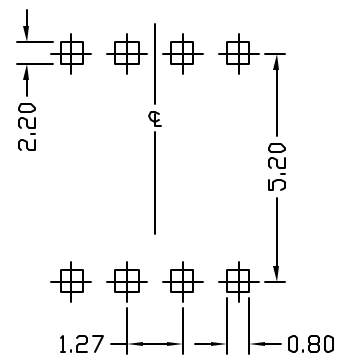
- NOTE:  
 1. LEAD FINISH: LEAD FREE COATING  
 2. TOLERANCE ± 0.10 mm (4 mil) UNLESS OTHERWISE SPECIFIED  
 3. COPLANARITY : 0.10 mm  
 4. DIMENSION L IS MEASURED IN GAGE PLANE

**PACKAGE MARKING DESCRIPTION**



- NOTE:  
 LOGO - AOS LOGO  
 4407 - PART NUMBER CODE, Lead\_Free  
 F - FAB LOCATION  
 A - ASSEMBLY LOCATION  
 Y - YEAR CODE  
 W - WEEK CODE  
 L T - ASSEMBLY LOT CODE

**RECOMMENDED LAND PATTERN**



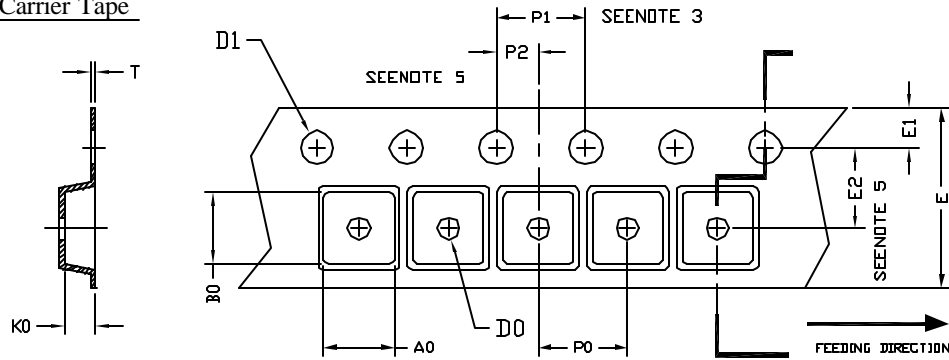
UNIT: mm

**SO-8 PART NO. CODE**

PART NO.	CODE
AO4407L	4407



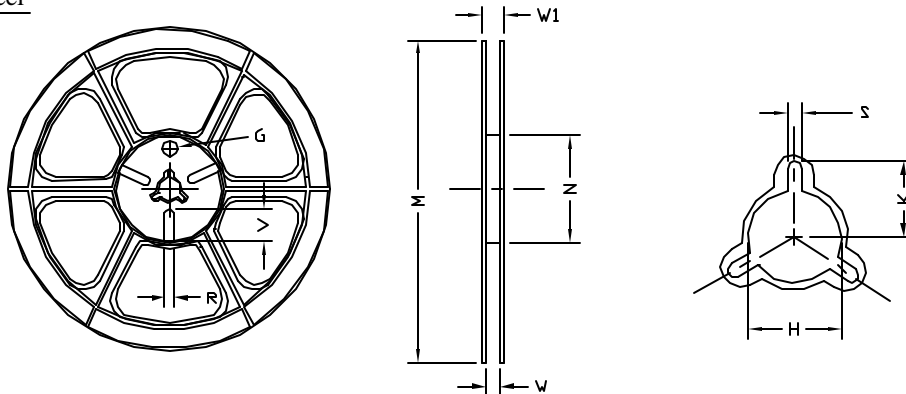
SO-8 Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SO-8 (12 mm)	6.40 ±0.10	5.20 ±0.10	2.10 ±0.10	1.60 ±0.10	1.30 +0.10	12.00 ±0.30	1.75 ±0.10	5.50 ±0.05	8.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.25 ±0.05

SO-8 Reel



UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	φ330	φ330.00 ±0.50	φ97.00 ±0.10	13.00 ±0.30	17.40 ±1.00	φ13.00 +0.50 -0.20	10.60	2.00 ±0.50	---	---	---

SO-8 Tape

Leader / Trailer  
& Orientation

